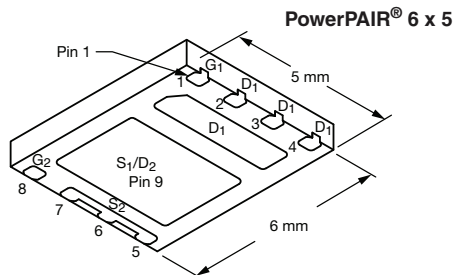




Dual N-Channel 30 V (D-S) MOSFETs

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A) ^g	Q _g (Typ.)
Channel-1	30	0.0064 at V _{GS} = 10 V	16 ^a	7.2 nC
		0.0100 at V _{GS} = 4.5 V	16 ^a	
Channel-2	30	0.0013 at V _{GS} = 10 V	40 ^a	45 nC
		0.00175 at V _{GS} = 4.5 V	40 ^a	



Ordering Information:

SiZ916DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

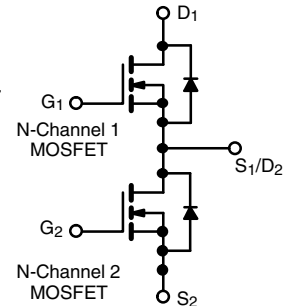
- TrenchFET® Gen IV Power MOSFETs
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- CPU Core Power
- Computer/Server Peripherals
- Synchronous Buck Converter
- POL
- Telecom DC/DC



RoHS
COMPLIANT
HALOGEN
FREE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Channel-1	Channel-2	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V _{GS}	± 20, - 16			
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	16 ^a	40 ^a	A	
	T _C = 70 °C		16 ^a	40 ^a		
	T _A = 25 °C		16 ^{a, b, c}	40 ^{a, b, c}		
	T _A = 70 °C		15.5 ^{b, c}	38.8 ^{b, c}		
Pulsed Drain Current (t = 300 μs)		I _{DM}	80	100		
Continuous Source Drain Diode Current	T _C = 25 °C	I _S	19	28		
	T _A = 25 °C		3.25 ^{b, c}	4.3 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	10	15		
Single Pulse Avalanche Energy		E _{AS}	5	11.25		
Maximum Power Dissipation	T _C = 25 °C	P _D	22.7	100	W	
	T _C = 70 °C		14.5	64		
	T _A = 25 °C		3.9 ^{b, c}	5.2 ^{b, c}		
	T _A = 70 °C		2.5 ^{b, c}	3.3 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260			

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	25	32	19	24	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	4.4	5.5	1	1.25	

Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 62 °C/W for channel-1 and 55 °C/W for channel-2.
- T_C = 25 °C.

SiZ916DT

Vishay Siliconix



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30			V	
		V _{GS} = 0 V, I _D = 250 μA	Ch-2	30				
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	Ch-1		17		mV/°C	
		I _D = 250 μA	Ch-2		8.8			
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	Ch-1		- 5.0			
		I _D = 250 μA	Ch-2		- 5.9			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.2		2.4	V	
		V _{DS} = V _{GS} , I _D = 250 μA	Ch-2	1		2.4		
Gate Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V, - 16 V	Ch-1			± 100	nA	
			Ch-2			± 100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA	
		V _{DS} = 30 V, V _{GS} = 0 V	Ch-2			1		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-1			5		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	Ch-2			5		
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-1	20			A	
		V _{DS} ≥ 5 V, V _{GS} = 10 V	Ch-2	25				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 19 A	Ch-1		0.0053	0.0064	Ω	
		V _{GS} = 10 V, I _D = 20 A	Ch-2		0.00105	0.00130		
		V _{GS} = 4.5 V, I _D = 15 A	Ch-1		0.0080	0.0100		
		V _{GS} = 4.5 V, I _D = 20 A	Ch-2		0.0014	0.00175		
Forward Transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 19 A	Ch-1		55		S	
		V _{DS} = 10 V, I _D = 20 A	Ch-2		116			
Dynamic ^a								
Input Capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		1208		pF	
			Ch-2		8082			
Output Capacitance	C _{oss}		Ch-1		375			
			Ch-2		1961			
Reverse Transfer Capacitance	C _{rss}	Channel-2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		30			
			Ch-2		227			
C _r /C _i Ratio			Ch-1		0.025	0.050		
			Ch-2		0.028	0.056		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	Ch-1		17	26	nC	
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	Ch-2		106	160		
		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	Ch-1		7.2	11		
			Ch-2		45	68		
Gate-Source Charge	Q _{gs}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	Ch-1		3.6			
			Ch-2		23.2			
Gate-Drain Charge	Q _{gd}		Ch-1		0.94			
			Ch-2		5			
Output Charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	Ch-1		10			
			Ch-2		57.5			
Gate Resistance	R _g	f = 1 MHz	Ch-1	0.5	2.5	5.0	Ω	
			Ch-2	0.2	1	2		

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit		
Dynamic ^a								
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1		16	24	ns	
			Ch-2		36	54		
Rise Time	t _r		Ch-1		11	20		
			Ch-2		55	83		
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1		15	23		
			Ch-2		44	66		
Fall Time	t _f		Ch-1		5	10		
			Ch-2		8	16		
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1		10	20		
			Ch-2		18	27		
Rise Time	t _r		Ch-1		10	20		
			Ch-2		10	20		
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1		20	30		
			Ch-2		45	68		
Fall Time	t _f		Ch-1		5	10		
			Ch-2		8	16		
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	Ch-1			40	A	
			Ch-2			40		
Pulse Diode Forward Current ^a	I _{SM}		Ch-1			80		
			Ch-2			100		
Body Diode Voltage	V _{SD}	I _S = 10 A, V _{GS} = 0 V	Ch-1		0.8	1.2	V	
		I _S = 10 A, V _{GS} = 0 V	Ch-2		0.8	1.2		
Body Diode Reverse Recovery Time	t _{rr}	Channel-1 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		15	23	ns	
			Ch-2		65	98		
Body Diode Reverse Recovery Charge	Q _{rr}		Channel-2 I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		4	8	nC
				Ch-2		52	78	
Reverse Recovery Fall Time	t _a			Ch-1		9		ns
				Ch-2		30		
Reverse Recovery Rise Time	t _b		Ch-1		6			
			Ch-2		22			

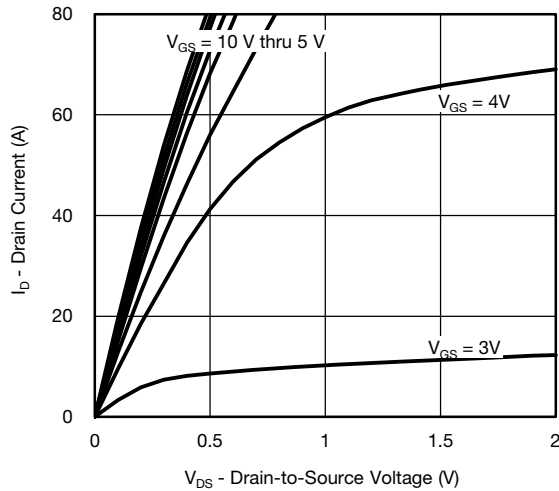
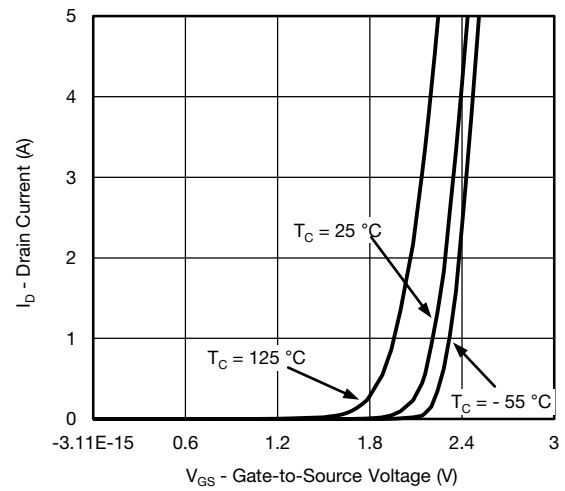
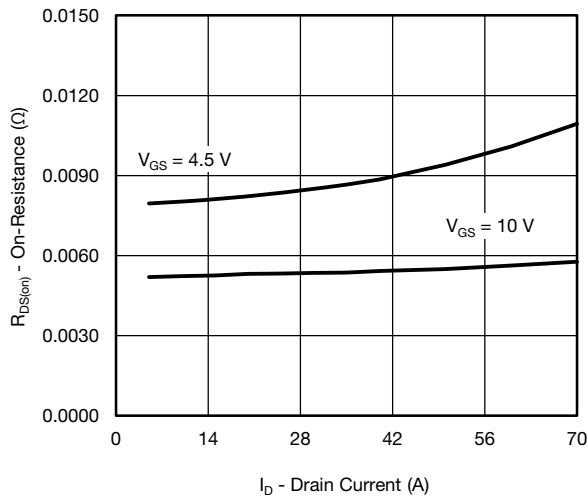
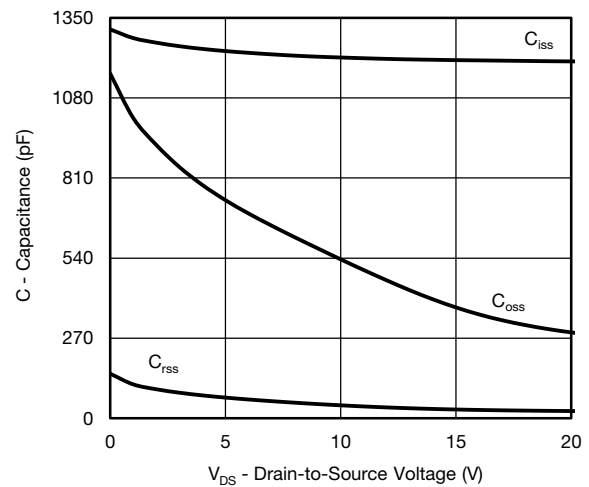
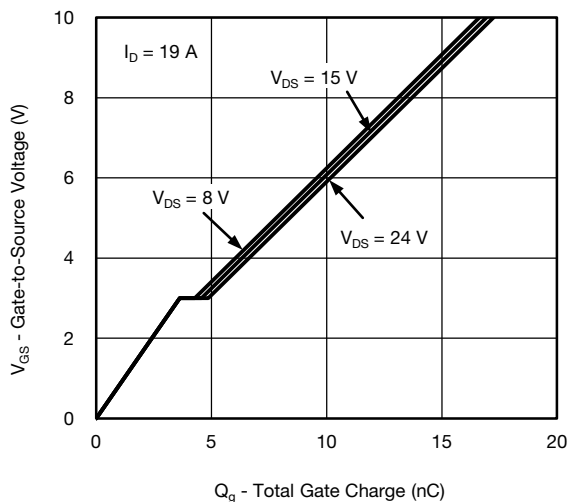
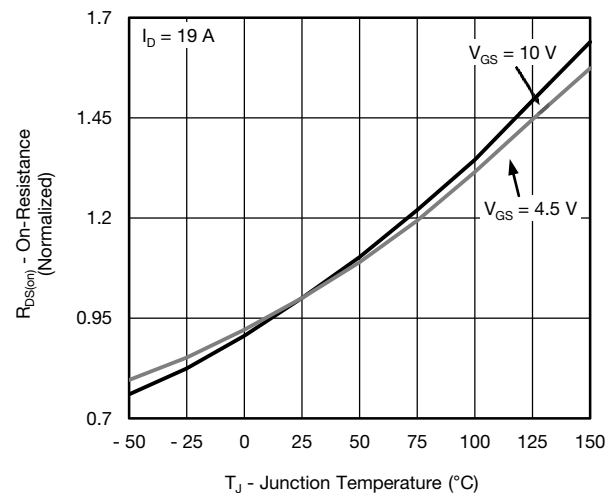
Notes:

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

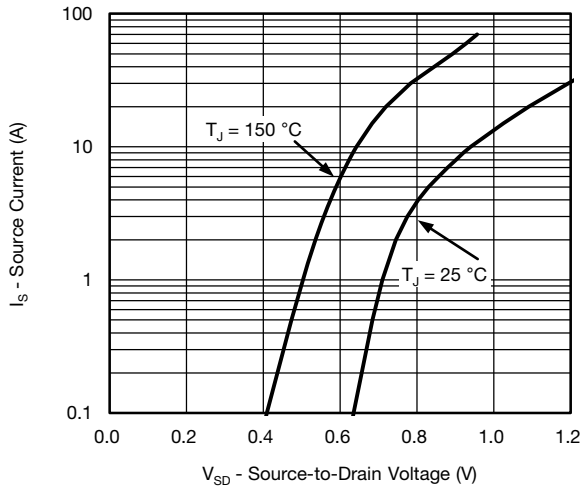
SiZ916DT

Vishay Siliconix

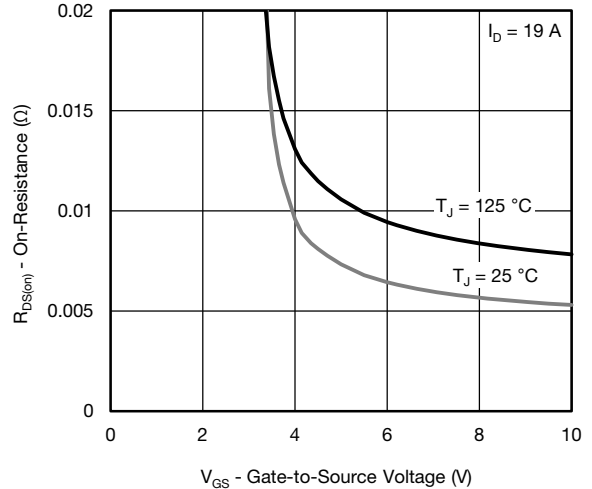
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**



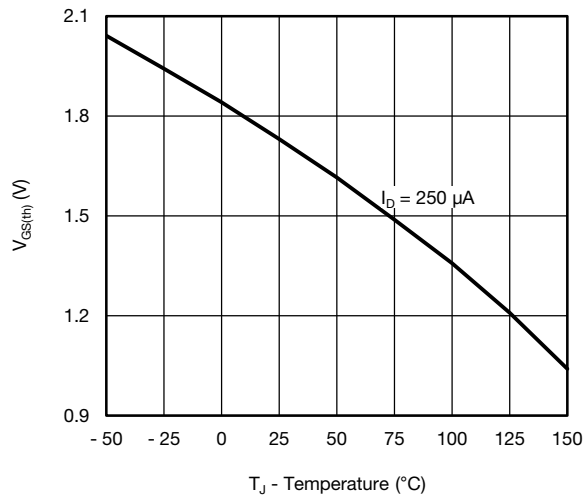
CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



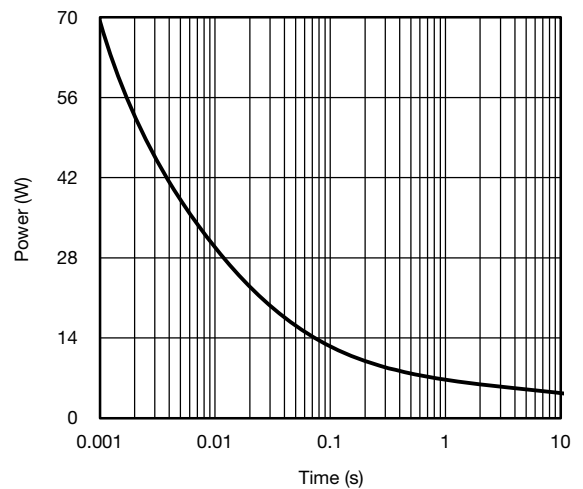
Source-Drain Diode Forward Voltage



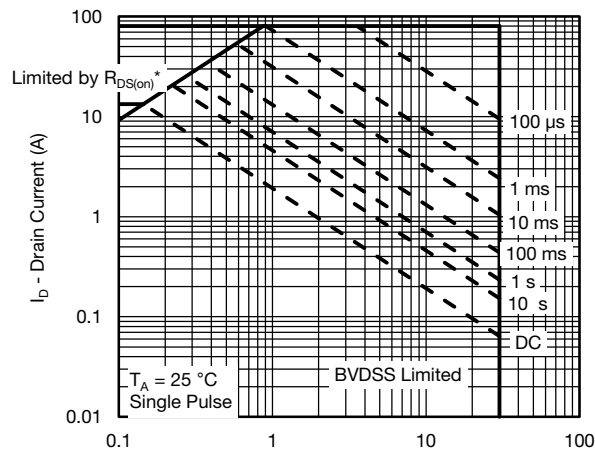
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



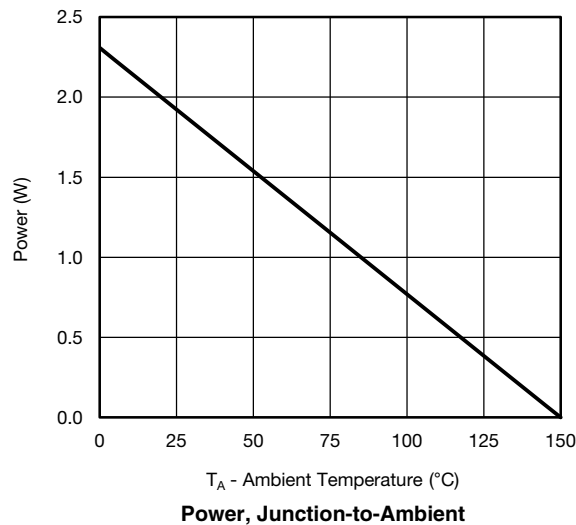
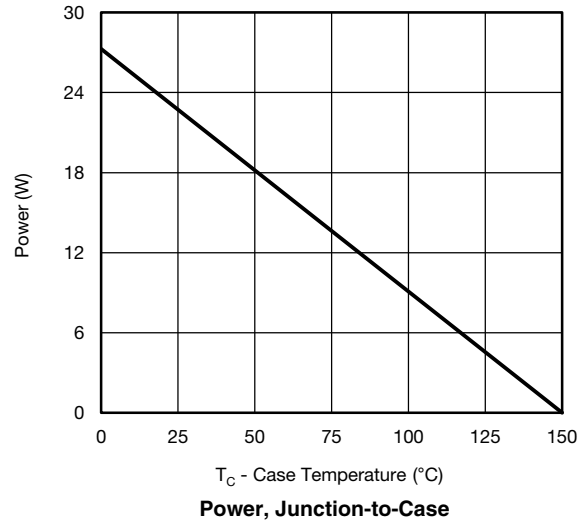
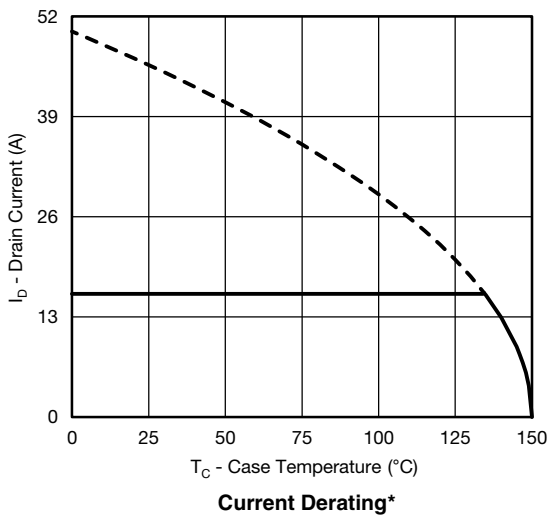
Single Pulse Power



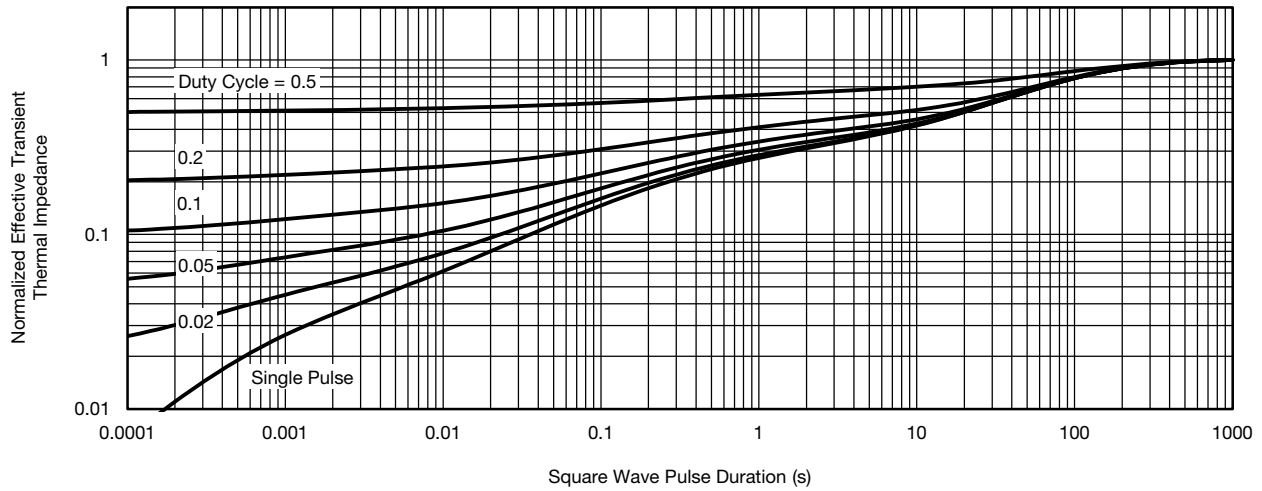
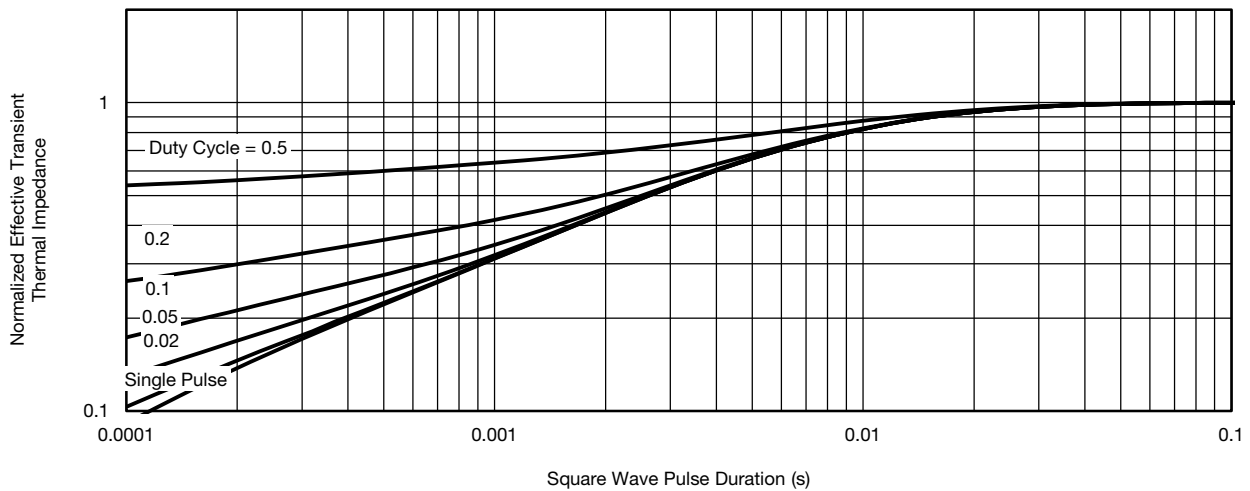
V_{DS} - Drain-to-Source Voltage (V)
 $* V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$
Safe Operating Area, Junction-to-Ambient

SiZ916DT

Vishay Siliconix

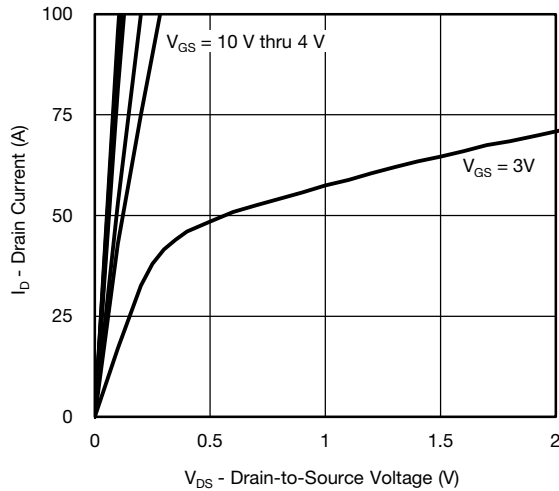
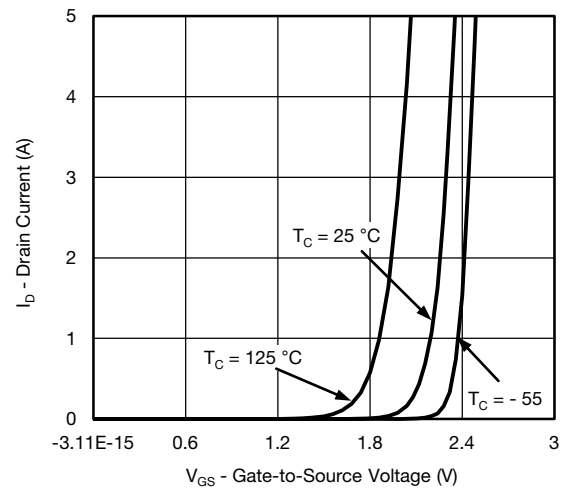
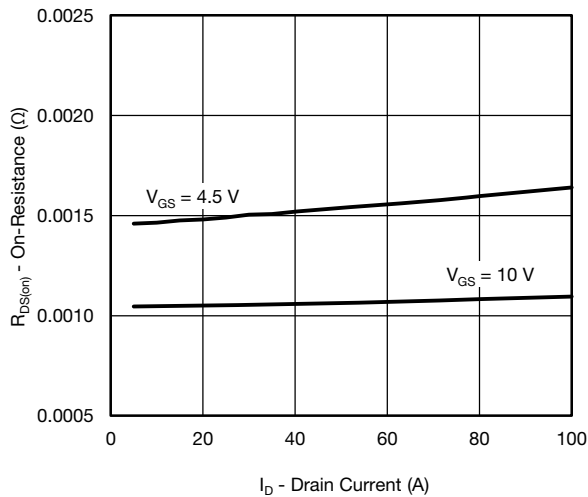
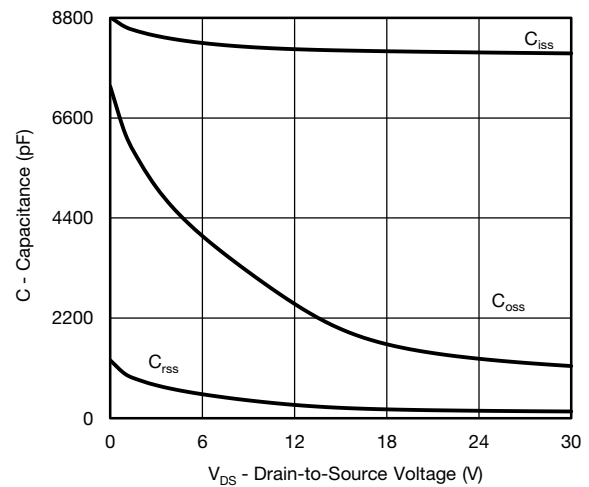
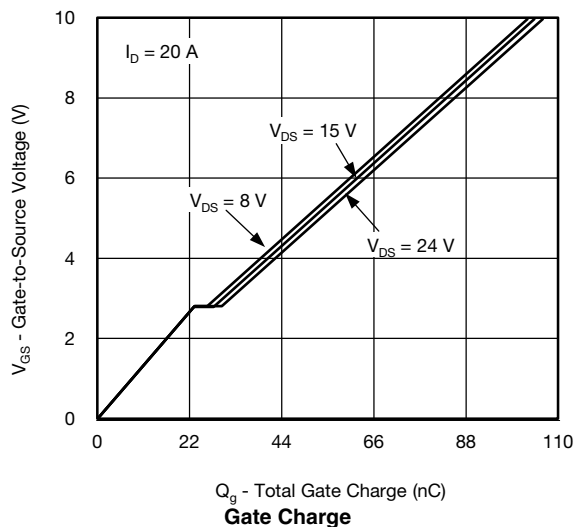
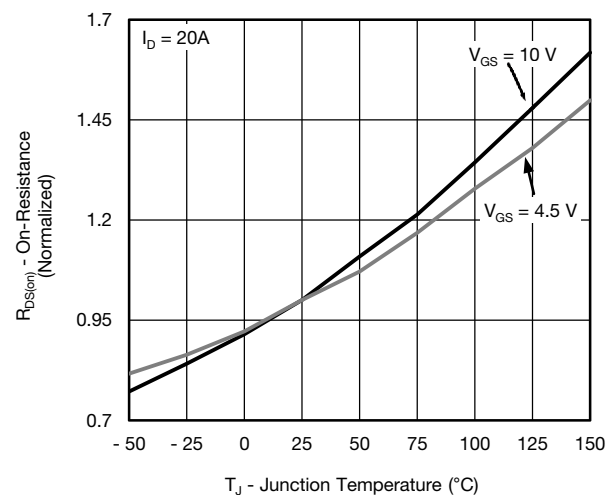
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

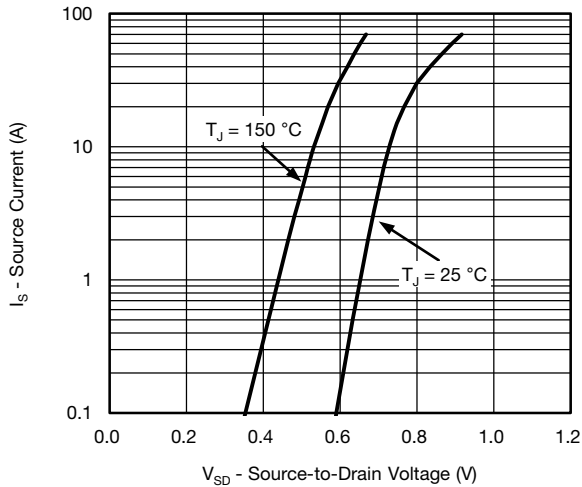
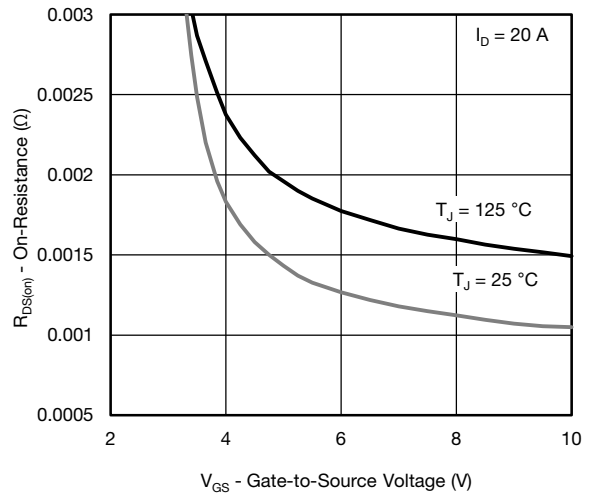
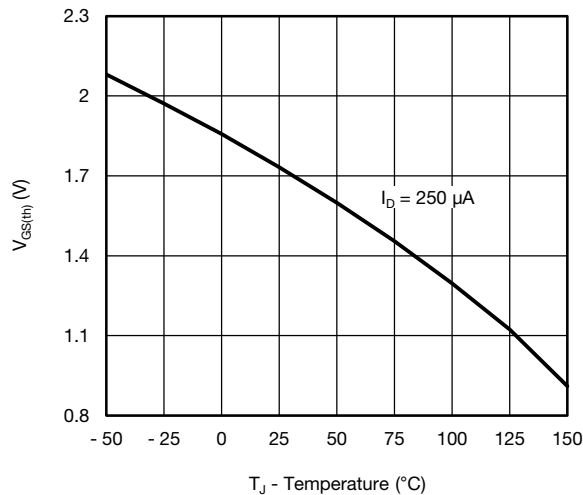
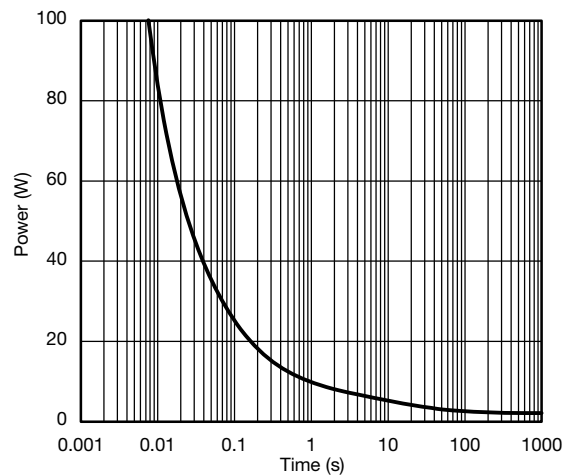
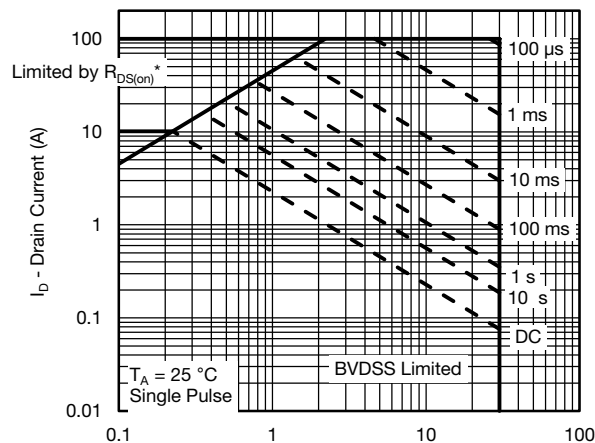
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.


CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

SiZ916DT

Vishay Siliconix

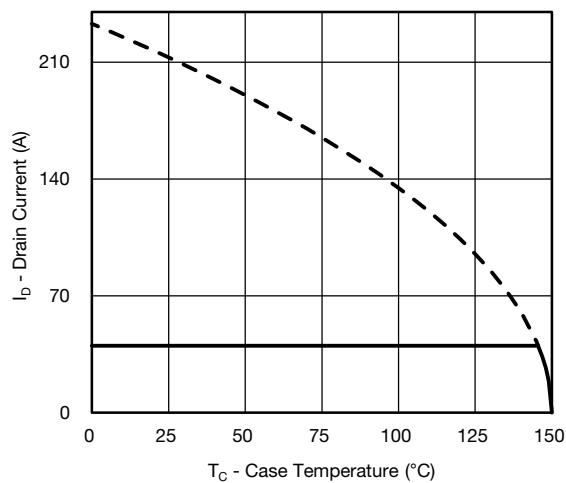
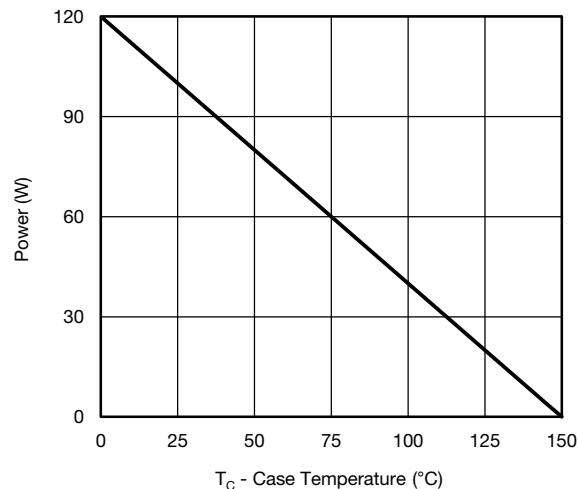
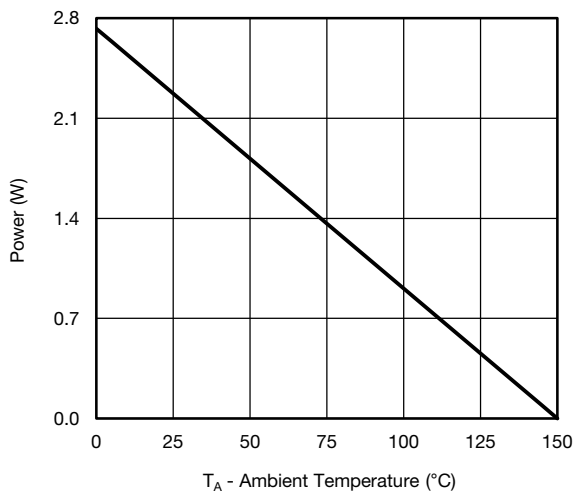
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**


CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power


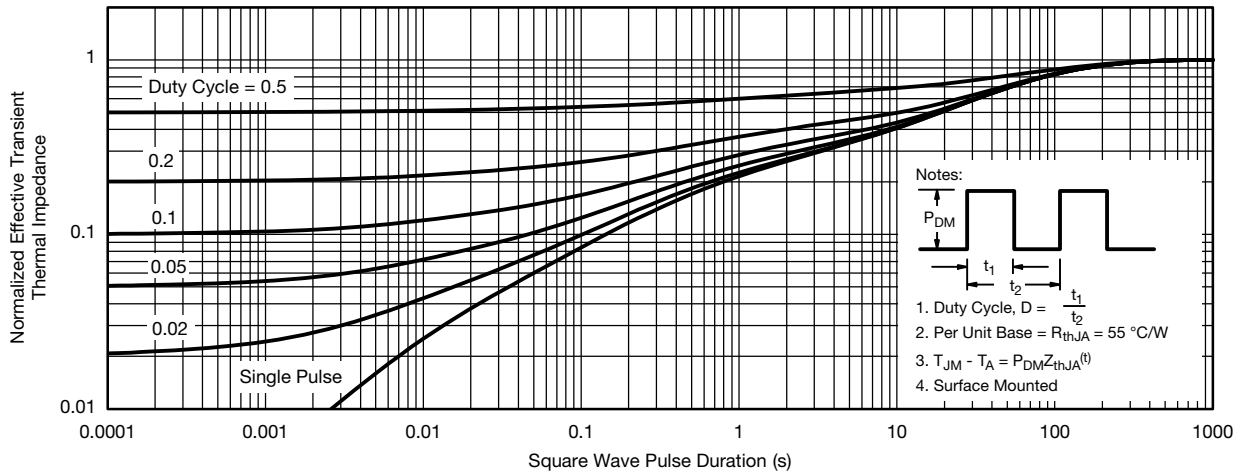
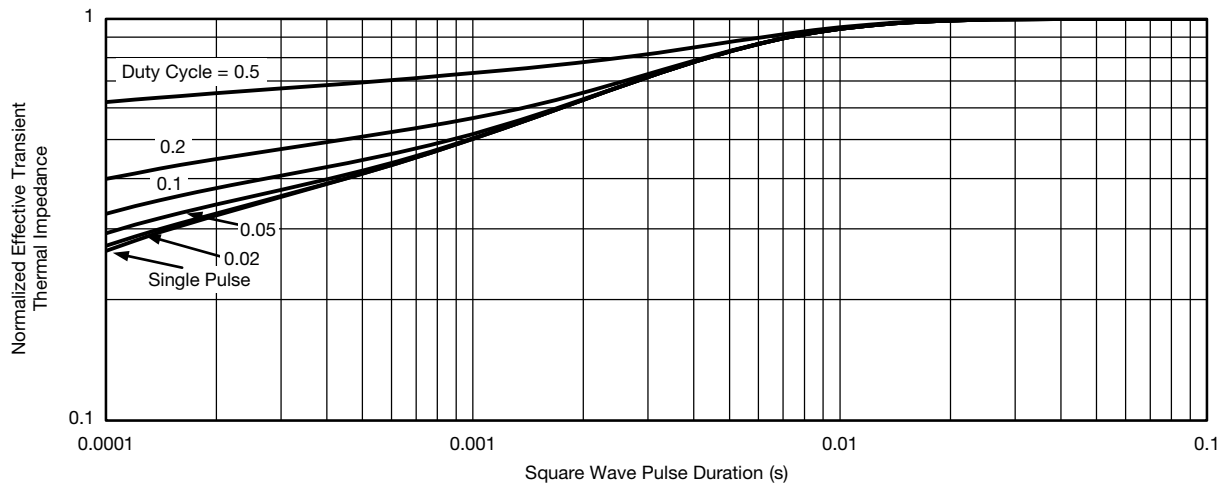
V_{DS} - Drain-to-Source Voltage (V)
 * $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

SiZ916DT

Vishay Siliconix

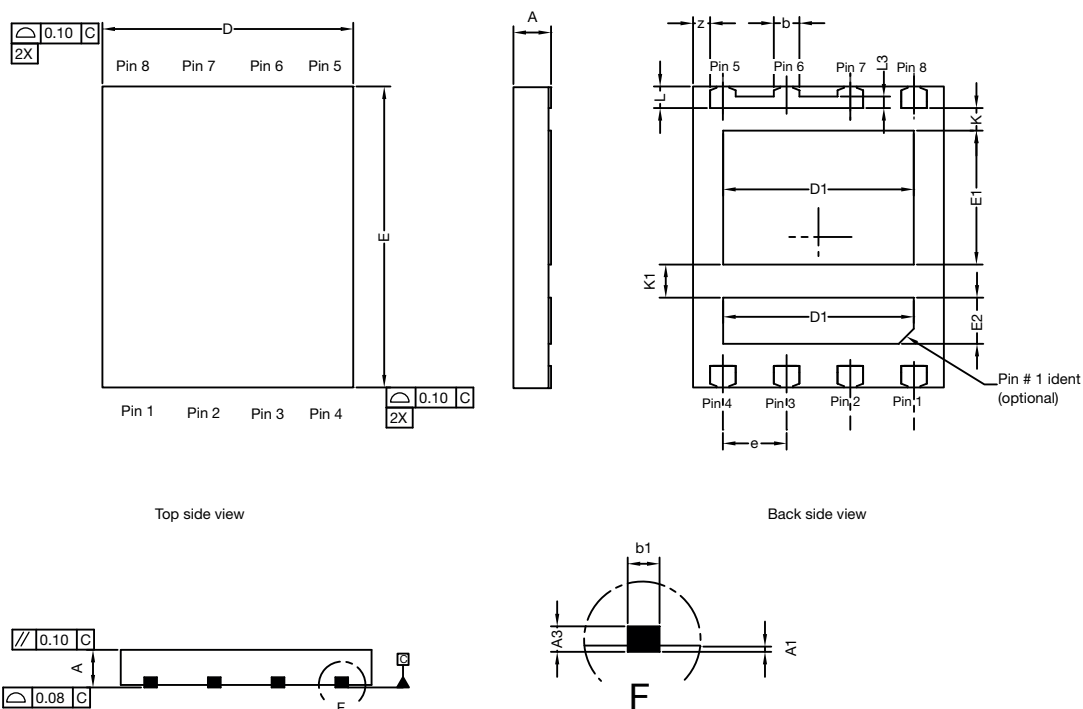
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Current Derating*****Power, Junction-to-Case****Power, Junction-to-Ambient**

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.


CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

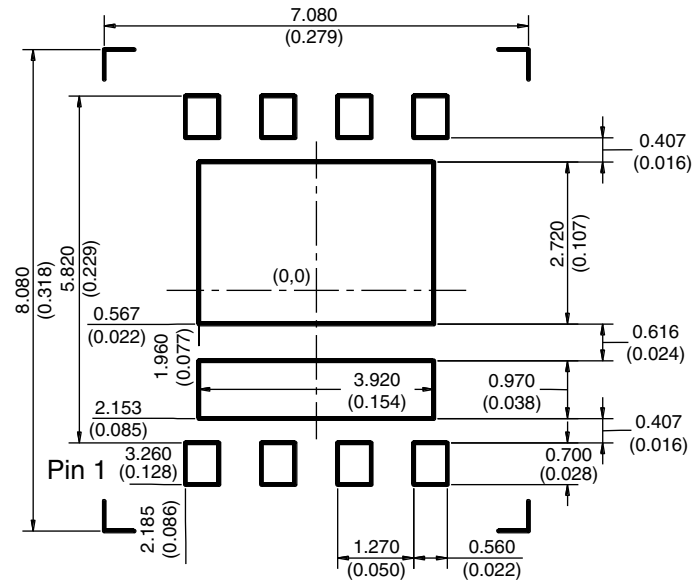
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62721.

PowerPAIR® 6 x 5 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	-	0.10	0.000	-	0.004
A3	0.15	0.20	0.25	0.006	0.007	0.009
b	0.43	0.51	0.61	0.017	0.020	0.024
b1	0.25 BSC			0.010 BSC		
D	4.90	5.00	5.10	0.192	0.196	0.200
D1	3.75	3.80	3.85	0.148	0.150	0.152
E	5.90	6.00	6.10	0.232	0.236	0.240
E1 Option AA (for W/B)	2.62	2.67	2.72	0.103	0.105	0.107
E1 Option AB (for BWL)	2.42	2.47	2.52	0.095	0.097	0.099
E2	0.87	0.92	0.97	0.034	0.036	0.038
e	1.27 BSC			0.050 BSC		
K Option AA (for W/B)	0.45 typ.			0.018 typ.		
K Option AB (for BWL)	0.65 typ.			0.025 typ.		
K1	0.66 typ.			0.025 typ.		
L	0.33	0.43	0.53	0.013	0.017	0.020
L3	0.23 BSC			0.009 BSC		
z	0.34 BSC			0.013 BSC		
ECN: T14-0782-Rev. C, 22-Dec-14						
DWG: 6005						

RECOMMENDED MINIMUM PAD FOR PowerPAIR® 6 x 5



Recommended Minimum Pad
Dimensions in mm (inches)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.